

Amendments to the Claims:

This listing of Claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1(currently amended):

A processing method for forming silicide comprising:

providing a semiconductor structure having a semiconductor surface and an insulation surface;

forming an epitaxial layer on said semiconductor surface together with residues of said epitaxial layer on said insulation surface;

treating said semiconductor structure, wherein said treating step is that [[the]] a removal rate of said residues of said epitaxial layer on said insulation surface is faster higher than [[the]] a removal rate of said epitaxial layer on said semiconductor surface;

forming a metal layer on said epitaxial layer; and

heating said epitaxial layer for forming silicide.

Claim 2(original):

The processing method according to claim 1, wherein providing said semiconductor structure step comprises forming a substrate and forming a gate electrode for forming a portion of said semiconductor structure.

Claim 3(original):

The processing method according to claim 2, wherein forming said semiconductor surface step comprises forming a doped region in said substrate for forming a portion of said semiconductor surface.

Claim 4(original):

The processing method according to claim 2, wherein forming said semiconductor surface step comprises forming an upper surface on said gate electrode for forming a portion of said semiconductor surface.

Claim 5(original):

The processing method according to claim 2, wherein forming said insulation surface step comprises forming a spacer on the sidewall of said gate electrode for forming a portion of said insulation surface.

Claim 6(original):

The processing method according to claim 2, wherein forming said insulation surface step comprises forming an insulation device in said substrate for forming a portion of said insulation surface.

Claim 7(original):

The processing method according to claim 1, wherein forming said epitaxial layer comprises forming epitaxial silicon.

Claim 8(original):

The processing method according to claim 1, wherein forming said epitaxial layer comprises forming an epitaxial silicon compound.

Claim 9(original):

The processing method according to claim 1, wherein said treating step comprises executing wet etching for removing a portion of said insulation surface.

Claim 10(original):

The processing method according to claim 9, wherein said wet etching comprises using fluorine-containing solution.

Claim 11(original):

The processing method according to claim 1, wherein said treating step comprises executing dry etching for removing a portion of said insulation surface.

Claim 12(original):

The processing method according to claim 11, wherein said dry etching comprises using a fluorine-containing compound.

Claim 13(original):

The processing method according to claim 1, wherein forming said metal layer comprises forming a titanium (Ti) layer.

Claim 14(original):

The processing method according to claim 1, wherein forming said metal layer comprises forming a cobalt (Co) layer.

Claim 15(currently amended):

A processing method for forming silicide comprises:

- providing a silicon substrate;
- forming a polysilicon gate electrode on said silicon substrate;
- forming an insulation spacer on ~~[[the]]~~ a sidewall of said polysilicon gate electrode;
- forming an epitaxial layer on said silicon substrate and an upper surface of said polysilicon gate electrode together with residues of said epitaxial layer on said insulation spacer;
- etching said residues of said epitaxial layer, said epitaxial layer and a portion of said insulation spacer, wherein a removal rate of said residues of said epitaxial layer on said insulation spacer is higher than a removal rate of said epitaxial layer on said silicon substrate and said upper surface of said polysilicon gate electrode;
- forming a metal layer on said epitaxial layer; and
- heating said epitaxial layer for performing salicidation on said upper surface of said polysilicon gate electrode and said silicon substrate.

Claim 16(original):

The processing method according to claim 15, wherein said etching step comprises executing wet etching with fluorine-containing solution.

Claim 17(original):

The processing method according to claim 15, wherein said etching step comprises executing dry etching with fluorine-containing compound.